Different title and authorship than the other 3 papers.

E. Andronescu and S. Jinga were added after the ECERS paper, although there is virtually no new content.

ANNEALING EFFECTS ON PROPERTIES OF Ba(Zn_{1/3}Ta_{2/3})O₃ DIELECTRIC MATERIALS

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EDX is missing, but EDX analysis is performed (see page 2), the same as in the TSF and ECERS papers, which mention EDX

in the abstract.

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Abstract - $Ba(Zn_{1/3}Ta_{2/3})O_3$ dielectric materials were prepared by solid state reaction. The samples were sintered at temperatures in the range $1400 \div 1600\,^{\circ}C$ for 4 h. Morphostructural characterization was performed by using SEM and XRD. The dielectric properties were measured in the microwave range $(6 \div 7\,\text{GHz})$. An additional annealing at $1400\,^{\circ}C$ for $10\,\text{hours}$ was performed in order to improve the dielectric parameters. The best parameters were achieved for the samples sintered at $1600\,^{\circ}C$ with additional thermal treatment.

Keywords: BZT, thermal treatment, microwaves

1. INTRODUCTION

Ba(B'_{1/3}B''_{2/3})O₃ complex perovskites are very attractive materials for very high frequency applications due to owing to their attractive properties, especially the ultra high values of the quality factor Q. Ba(Zn_{1/3}Ta_{2/3})O₃ compound (BZT) has potential for applications in satellite broadcasting at frequencies higher than 10 GHz and as a very high Q dielectric resonators (DR) in mobile phone base stations or combiner filter for PCS applications [1]. The BZT ceramics exhibit a dielectric constant of 29, a $Q \times f$ product of $100,000 \div 160,000$ GHz and a low temperature coefficient of resonant frequency τ_f close to zero in the presence of such additives as strontium-gallium [2].

There are several factors, which influence the *Q* values of perovskites Ba(M_{1/3}²⁺ Ta_{2/3}⁵⁺)O₃ with M=Mg, Zn such as: the long range ordering (LRO) of cations, the zinc oxide evaporation, the point defects and the stabilization of the microdomain boundaries [2]. The high Q values were explained from the point of view of the lattice vibrations of its trigonal superstructure. Sagala et Nambu calculated the dielectric loss tangent in microwaves from the equation of ion motions, which was a function of B-site ordering

[3]. Galasso and co-workers concluded that the B-site ordering increased as the difference in charge and size between B' and B" atoms increased [4]. The ordering of complex perovskite BZT is important because the 1:2 ordering of the B' and B" cations along the <111> axis is believed to be closely related to the high-Q property of BZT. There is a strong correlation between the cation ordering degree, domain growth, zinc loss and sintering parameters. The synthesis of a BZT material, its structural and morphologic characteristics as well as its microwave dielectric properties correlated to the thermal treatments parameters are reported.

2. METHODS

Ba($Zn_{1/3}Ta_{2/3}$)O₃ samples were prepared by solid-state reaction. The starting materials were BaCO₃, ZnO and Ta₂O₅. Stoichiometric quantities were weighted, ground, homogenized and milled in an agate mill in water for two hours. The powders were calcined at T = 925 °C for two hours. Then the powders were milled for 2 h and calcined at 1000 °C/ 2 h. The third calcination was carried out at T = 1150 °C/2.5 h, in air. The triple calcined powders were mixed with 1 % polyvinyl alcohol (PVA) and dried at T = 80 °C, then were pressed into cylindrical samples of 12 mm diameter and 10 mm height. The pellets were slowly dried at 80 °C in order to eliminate the PVA.

The density of green ceramics was $\rho = 4400 \text{ kg/m}^3$. The sintering treatment for the BZT samples was performed in air for 4 h at five different temperatures: $1400 \,^{\circ}\text{C}$, $1450 \,^{\circ}\text{C}$, $1500 \,^{\circ}\text{C}$, $1525 \,^{\circ}\text{C}$, and $1600 \,^{\circ}\text{C}$. In order to improve the dielectric properties, especially the quality factor Q, the samples were treated supplementary for $10 \, \text{h}$ at $1400 \,^{\circ}\text{C}$. The pellets were polished in

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function of B-site or

order to remove the superficial zone and to obtain correct values of the microwave dielectric parameters.

The relative bulk density of sintered disks was measured by the Archimedes method. Morphological, structural and compositional analyses were performed on 5 sets of samples by X-ray diffraction (XRD) analysis, and electron microscopy (SEM, EDX). The patterns were recorded in a 2θ range from 20° and 90° on a Seifert Debye Flex 2002 diffractometer into the $2\theta - \theta$ mode. Measurements were performed at room temperature using Cu K_{\alpha} radiation, Ni filter and a detector scan speed of 7° /min.

The dielectric parameters, i.e. the dielectric constant ε_r , the quality factor Q and the loss tangent $tan \delta$ were measured in the microwave range by Hakki-Coleman method. A computer aided measurement system containing a HP 8757 C scalar network analyzer and a HP 8350 B sweep oscillator was employed.

3. RESULTS

The bulk density of the fired BZT ceramics was measured after grinding and polishing. The temperature dependence of densification after 4 h sintering in air is shown in Fig 1. BZT ceramics sintered between 1500 °C and 1600 °C were well sintered.

The X-ray density of Ba($Zn_{1/3}Ta_{2/3}$)O₃ ceramic is $\rho_t = 7920 \text{ Kg/m}^3$. The most dense ceramics exhibit a porosity value of 10%. An abnormal grain growth together with an accentuated ZnO evaporation occurred above the sintering temperature $T_s = 1525 \,^{\circ}\text{C}$, so the bulk density slightly decreased. Above $T_s = 1525 \,^{\circ}\text{C}$, the bulk density continued to increase.

Same graph as TSF and ROMJIST. The ECERS paper has a table with the same values, Table 1 (Bulk density and Porosity columns).

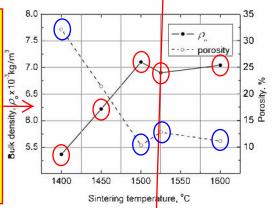


Fig. 1. Bulk density versus simering temperature for BZT samples.

The X-ray diffraction patterns for BZT ceramic samples sintered at five sintering temperatures are given in Fig.2. The patterns confirm the formation of the hexagonal structure, which is the majority phase. For the BZT compounds sintered at $T_s = 1525$ °C the patterns reveal the presence of secondary phases Ba₇Ta₆O₂₂, Ba₈ZnTa₂₄ and BaO, which disappear at higher sintering temperatures. The superlattice peaks at $2\theta = 17.6$ and 26.4 degrees increase in intensity with the increase of T_s up to 1525 °C. At $T_s = 1600$ °C they practically disappear. For temperatures up to 1525 °C, the LRO gradually increases with the temperature increase

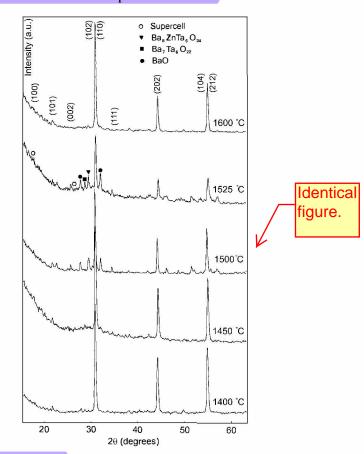


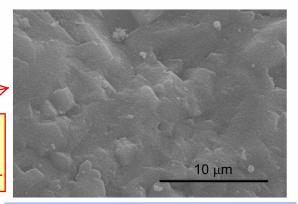
Fig. 2. XRD patterns of $Ba(Zn_{1/3}Ta_{2/3})O_3$ system versus sintering temperature.

The microstructure of BZT ceramics sintered in air at 1500 °C/4h and 1600 °C/4h was investigated by using SEM. The images are presented in Figs. 3-4. The micrograph presents a bimodal distribution of the grains size for BZT sample sintered at 1500 °C. Micron grains are located on the grain boundaries or on the grain surfaces; some grains with size in the range

In the ECERS and TSF articles, this result is cited from different authors, namely [6] Roulland et al. That citation is missing here, and those authors do not appear in the reference list in this article.

Same values as ROMJIST but different to TSF, although the numerical values and graphs are the same.

3 ÷ 6 μm are polyhedral with rounded/corners and not well faceted and others are spherical with sizes up to 1.5 μm. Well faceted, polyhedral grains with smooth surfaces and vedges and dimensions in the range (10 \$30) μm are observed for BZT sample sintered at 1600 °C. The abnormal granular growth together with the ZnO evaporation can explain the non-monotonic variation of the BZT bulk density with T_s , for $T_s > 1500$ °C. The relatively small difference between 1500 °C and 1600 °C sintering temperatures has as effect a strong granular growth, as can be noticed in Fig.3 and Fig.4.



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ROMJIST

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Fig. 3. Micrographs of the BZT sample sintered 1500°C/4h.

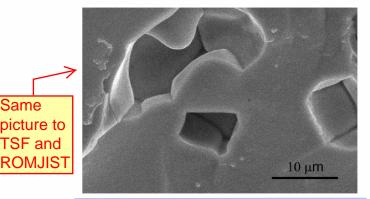


Fig. 4. Micrographs of the BZT sample sintered 1600°C/4h.

Microwave measurements on dielectric constant and loss tangent were carried out on the BZT samples. The obtained data revealed a determinant influence of the sintering temperature on the complex dielectric constant. The variation of the dielectric constant and dielectric loss with the sintering temperature can be observed in Fig. 5. This can be considered as an effect of the reduced porosity resulting in a better densification at high sintering temperatures, as can be seen in Fig. 1.

The loss tangent exhibits values around 2x10⁻⁴ for samples sintered at 1400 °C and 1450 °C. With the sintering temperature increase, the dielectric loss tangent increases up to 7x10⁻⁴ for $T_s = 1500$ °C, then decreases down to 2×10^{-4} for $T_s = 1600$ °C, as can be noticed in Fig. 5. This variation could be related to the Zn and Ta cation ordering process and with the secondary phases, which appear for sintering temperatures between 1450 °C and 1525 °C as shown in Fig. 2. For temperatures higher than 1525 °C, these phases disappear and, consequently, the dielectric loss decreases.

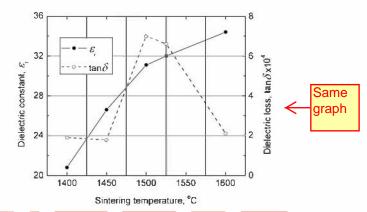


Fig. 5. Dielectric properties versus sintering temperature for BZT samples without annealing.

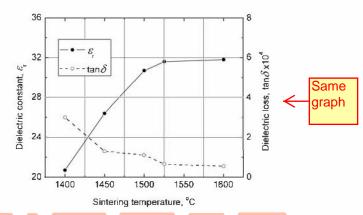


Fig. 6. Dielectric properties versus sintering temperature for annealed BZT samples.

The additional thermal treatment at 1400 °C for 10 h for all the samples resulted in the reduction of the BZT dielectric loss as can be seen in Fig. 6. For annealed samples, the dielectric loss continuously decreases with the increase of the sintering temperature. The dielectric constant values were not substantially modified by the annealing treatment, with only one exception of the BZT samples sintered at 1600 °C.

The quality factor *Q* values normalized at 10 GHz for the BZT samples are presented in figure 7. The *Q* is higher for annealed samples than for the samples without thermal treatment; this difference is more significant especially for BZT samples sintered beyond 1525 °C, which indicate the necessity of post sintering thermal treatment. The BZT samples sintered at 1600 °C exhibit a dielectric constant of about 31 and a quality factor normalized to 10 GHz up to 13500.

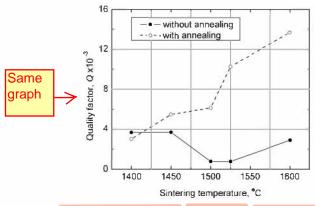
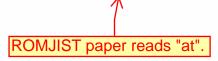


Fig. 7. Quality factor normalized at 10 GHz versus sintering temperature for BZT samples with and without annealing...

4. CONCLUSIONS

 $Ba(Zn_{1/3}Ta_{2/3})O_3$ ceramics with low loss in microwave domain were obtained by solid state reaction in the temperature range $1400 \div 1600$ °C.

For sintering temperatures higher then 1500 °C, the XRD patterns reveal the BZT multiphase compositions with the presence of trigonal supercell peaks and low Zn content secondary phases. The last two disappear at temperatures higher than 1600 °C.



The quality factor Q strongly depends on the BZT crystalline structure, that is on the unit cell distortion and cationic order. Dielectric loss decreases with the increase of ordering degree in the structure and with the disappearance of secondary phases. Lowest loss is obtained for a Zn and Ta completely ordered BZT ceramic with a strongly distorted unit cell. Porosity has small effect on dielectric loss of BZT material.

Well-sintered and annealed BZT samples exhibit a dielectric constant around 31 and a Qxf product up to 135,000 GHz. The achieved veryhigh values of the quality factor Q recommend the BZT materials for microwave and millimeter wave applications.

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References

- [1] S. Desu, H. M. O'Bryan, "Microwave loss quality of Ba(Zn_{1/3}Ta_{2/3})O₃ ceramics" J. Am. Ceram. Soc., vol.68, no. 10, pp. 546-551, 1985.
- [2] I. M. Reaney et al., "Ordering and quality factor in 0.95 BaZ 1_{1/3} Ta_{2/3}O₃ 0.05 SrGa_{1/2} Ta_{1/2}O₃ production resonators", *J. Eur. Ceram. Soc.*, vol. 23, no. 16, pp. 3021-3034, 2003.
- [3] D. A. Sagal, S. Nambu, "Microscopic calculation of dielectric loss at microwave for complex perovskite Ba(Zn_{1/3}Ta_{2/3})C₃", *J. Am. Ceram. Soc.*, vol. 75, no. 9, pp. 2573-2575, 1992.
- [4] F. Gallasso, J. Pyle, "Ordering of the compounds of the A(B′_{●,33} Ta_{●,66})O₃ type" *Inorg. Chem.*, vol. 2, no.3, pp. 482-484, 1983.

Different grant than the ECERS paper.